

BAS16W/BAV70W/BAW56W/BAV99W/BAL99W

List

List..... 1

Package outline..... 2

Features..... 2

Mechanical data..... 2

Maximum ratings 2

Rating and characteristic curves..... 3~4

Pinning information..... 5

Marking..... 5

Suggested solder pad layout..... 5

Packing information..... 6

Reel packing..... 6

Suggested thermal profiles for soldering processes..... 7

High reliability test capabilities..... 8

BAS16W/BAV70W/BAW56W/BAV99W/BAL99W

200mW Surface Mount Switching Diode- 75V

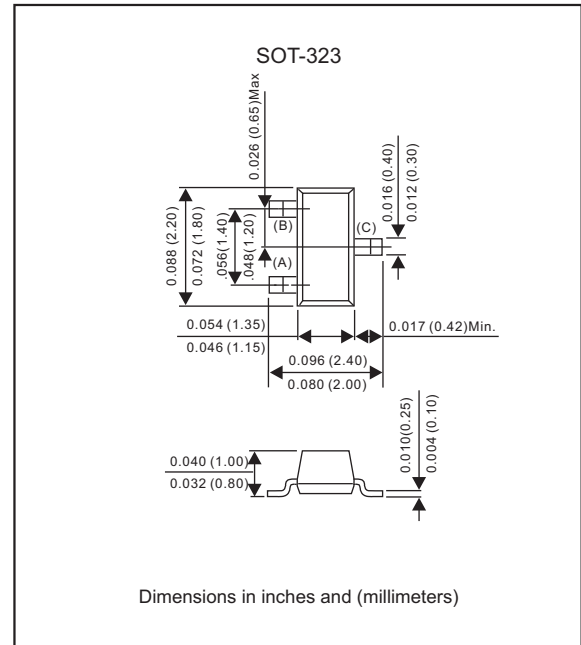
Features

- Fast speed switching.
- For general purpose switching application.
- High conductance.
- Silicon epitaxial planar chip.
- Lead-free parts meet RoHS requirements.
- Suffix "-H" indicates Halogen-free parts, ex. BAS16W-H.

Mechanical data

- Epoxy:UL94-V0 rated flame retardant
- Case : Molded plastic, SOT-323
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026
- Mounting Position : Any
- Weight : Approximated 0.006 gram

Package outline



Maximum ratings and Electrical Characteristics (AT $T_A=25^{\circ}\text{C}$ unless otherwise noted)

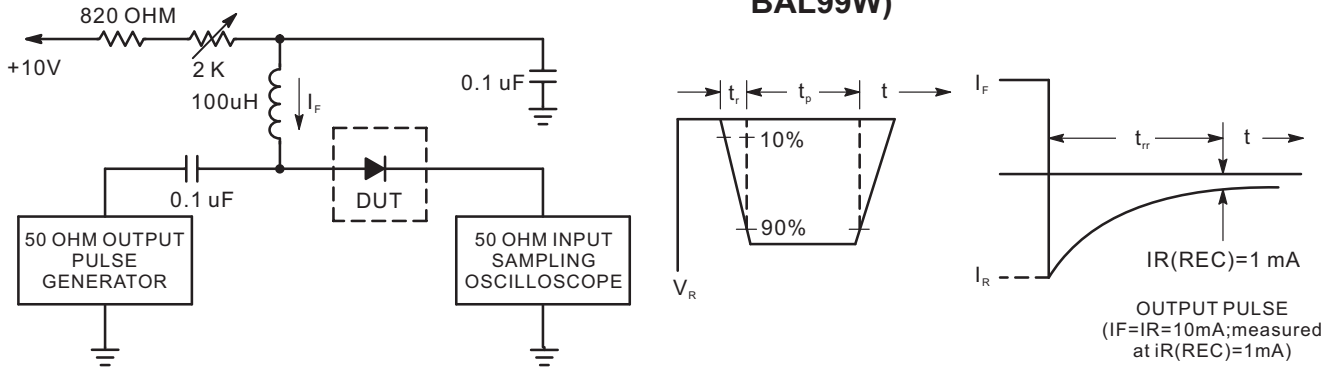
PARAMETER	Symbol	BAS16W	BAV70W	BAW56W	BAV99W	BAL99W	UNIT
Maximum Reverse Voltage	V_R	75					V
Maximum Forward Current	I_F	200			215		mA
Maximum Peak Forward Surge Current	I_{FM}	500					mA
Total Device Dissipation FR-5 Board* ¹ , $T_A = 25^{\circ}\text{C}$ Derate Above 25°C	P_D	200					mW
Maximum Thermal Resistance Junction to Ambient (Note 1)	$R_{\theta JA}$	1.6					$\text{mW}/^{\circ}\text{C}$
Total Device Dissipation Substrate* ² , $T_A = 25^{\circ}\text{C}$ Derate Above 25°C	P_D	300					mW
Maximum Thermal Resistance Junction to Ambient (Note 2)	$R_{\theta JA}$	2.4					$\text{mW}/^{\circ}\text{C}$
Operating Junction Temperature Range	T_J	-65 to +150					$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-65 to +150					$^{\circ}\text{C}$
Maximum Reverse Voltage Leakage Current at $V_R = 75\text{V}$ at $V_R = 70\text{V}$ at $V_R = 25\text{V}$, $T_J = 150^{\circ}\text{C}$ at $V_R = 75\text{V}$, $T_J = 150^{\circ}\text{C}$ at $V_R = 70\text{V}$, $T_J = 150^{\circ}\text{C}$	I_R	1.0 - 30.0 50.0 -	- 2.5 60.0 - 100.0	- 2.5 30.0 - 50.0	- 2.5 30.0 - 50.0	- 2.5 30.0 - 50.0	μA_{dc}
Typical Diode Capacitance ($V_R = 0\text{V}$, $f = 1.0\text{MHz}$)	C_D	2.0	1.5	2.0	1.5	1.5	pF
Maximum Reverse Recovery Time ($I_F = I_R = 10\text{mA}$, $V_R = 5.0\text{V}_{dc}$, $I_R(\text{REC}) = 1.0\text{mA}_{dc}$, $R_L = 100_{\Omega}$)	t_{rr}	6.0					ns
Maximum Forward Voltage at $I_F = 1.0\text{mA}_{dc}$ at $I_F = 10\text{mA}_{dc}$ at $I_F = 50\text{mA}_{dc}$ at $I_F = 150\text{mA}_{dc}$	V_F	715 855 1000 1250					mV

Notes:

*1 FR-5=1.0x0.75x0.062 in

*2 Alumina=0.4x0.3x0.024 in 99.5% Alumina

Rating and characteristic curves for each diode (BAS16W/BAV70W/BAW56W/BAV99W BAL99W)



- Notes : 1. A2.0 Kohm variable resistor adjusted for a forward Current (I_F) of 10mA.
 2. Input pulse is adjusted so $I_R(\text{peak})$ is equal to 10 mA.
 3. $t_p \gg t_{rr}$.

Recovery Time Equivalent Test Circuit

Power Derating Curve

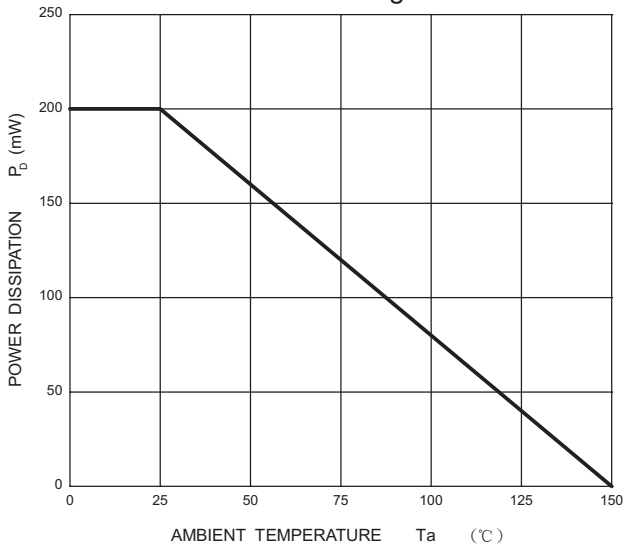


FIG.1-TYPICAL FORWARD CHARACTERISTICS

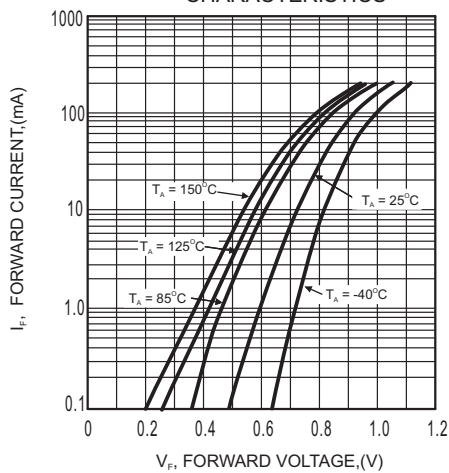
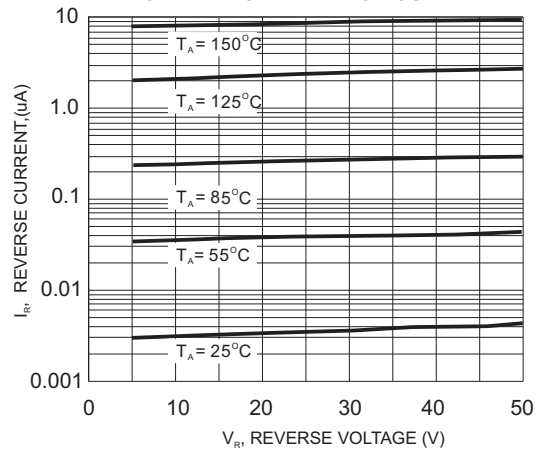


FIG.2 - TYPICAL LEAKAGE CURRENT



Rating and characteristic curves for each diode (BAS16W/BAV70W/BAW56W/BAV99W/BAL99W)

FIG.3 - DIODE CAPACITANCE (BAS16W)

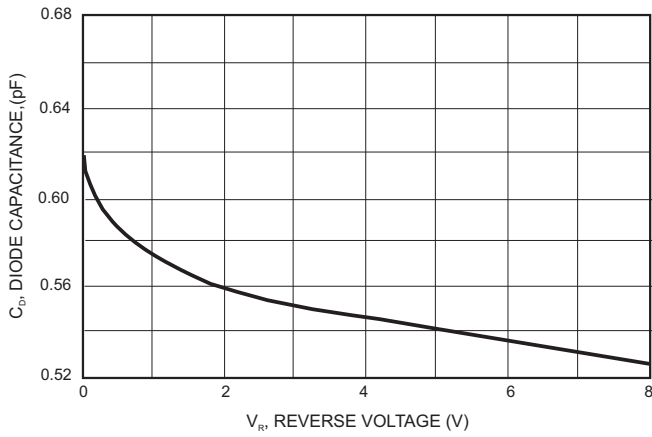


FIG.4 - DIODE CAPACITANCE (BAV70W)

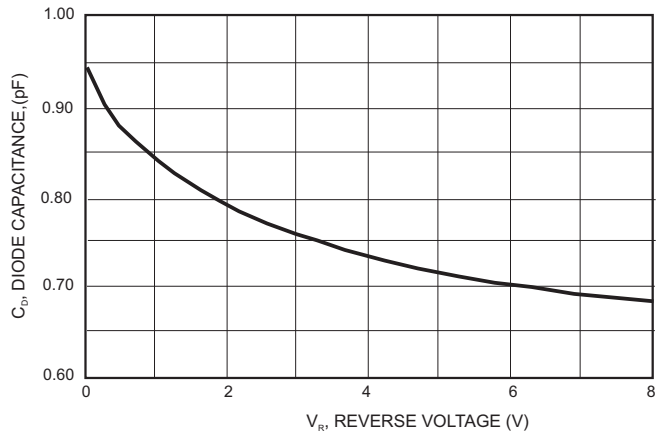


FIG.5 - DIODE CAPACITANCE (BAW56W)

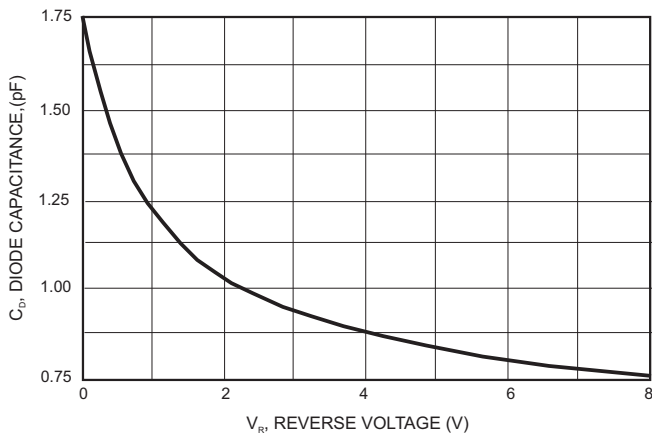


FIG.6 - DIODE CAPACITANCE (BAV99W)

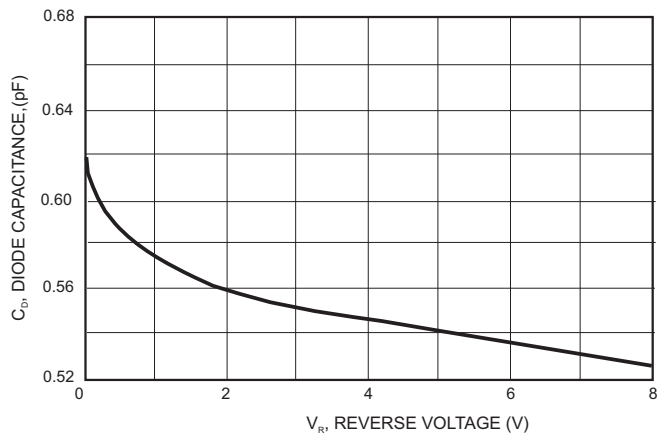
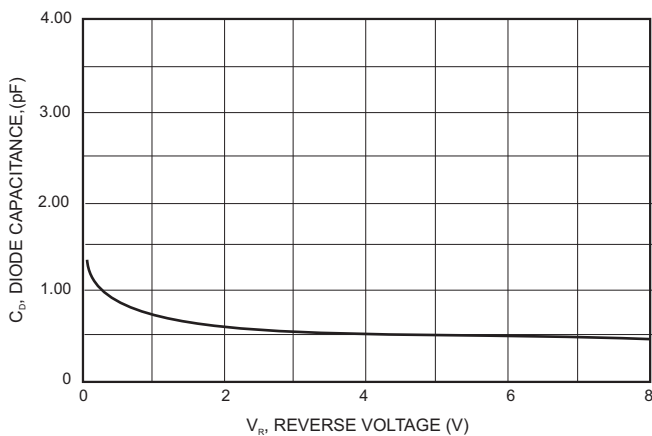


FIG.7 - DIODE CAPACITANCE (BAL99W)



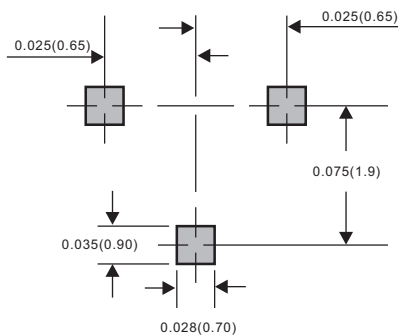
BAS16W/BAV70W/BAW56W/BAV99W/BAL99W

Pinning information

Type number	Marking code	Simplified outline	Symbol
BAS16W	A6		
BAV70W	A4, JA		
BAW56W	A1, JC		
BAV99W	A7, JB		
BAL99W	JF		

Suggested solder pad layout

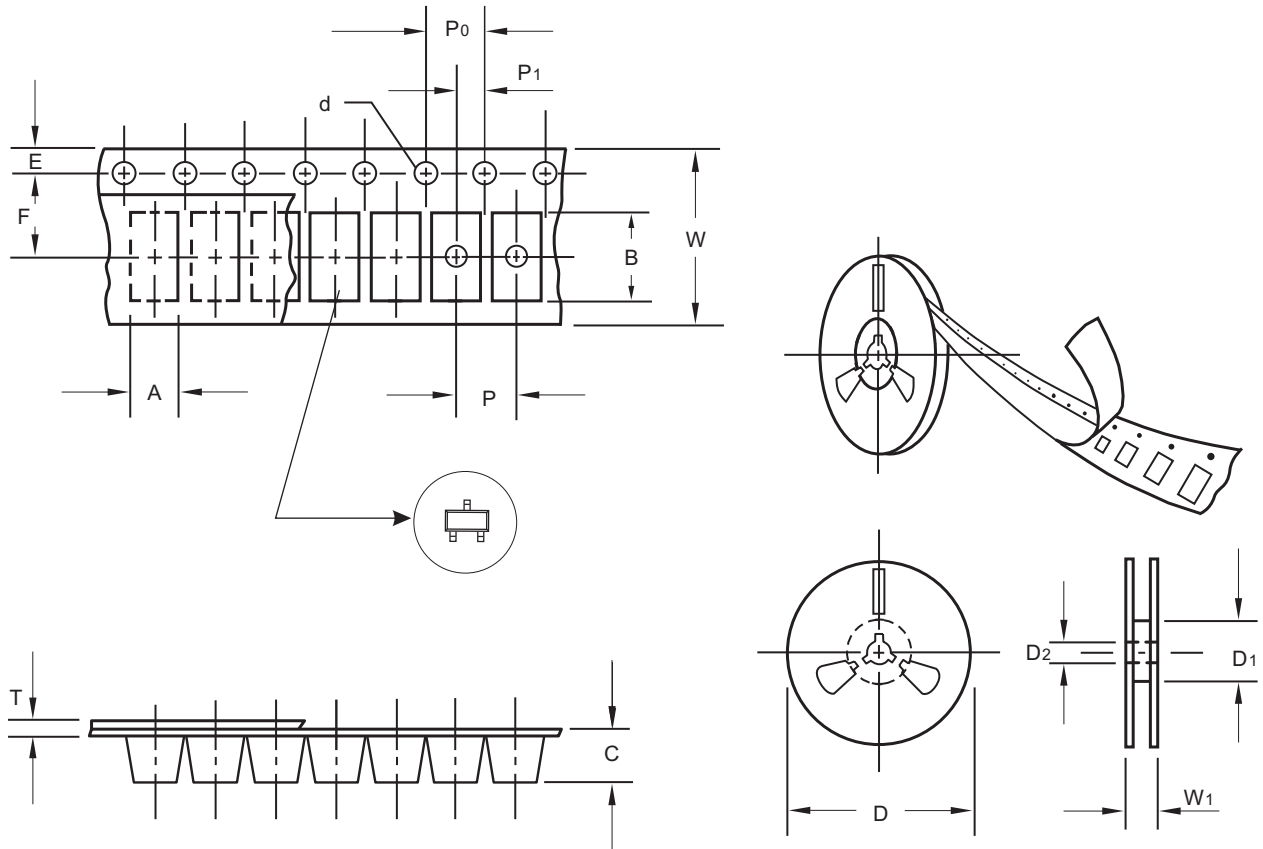
SOT-323



Dimensions in inches and (millimeters)

BAS16W/BAV70W/BAW56W/BAV99W/BAL99W

Packing information



unit:mm

Item	Symbol	Tolerance	SOT-323
Carrier width	A	0.1	2.36
Carrier length	B	0.1	2.40
Carrier depth	C	0.1	1.20
Sprocket hole	d	0.1	1.50
13" Reel outside diameter	D	2.0	-
13" Reel inner diameter	D1	min	-
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D1	min	62.00
Feed hole diameter	D2	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	3.50
Punch hole pitch	P	0.1	4.00
Sprocket hole pitch	P0	0.1	4.00
Embossment center	P1	0.1	2.00
Overall tape thickness	T	0.1	0.23
Tape width	W	0.3	8.00
Reel width	W1	1.0	11.40

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.

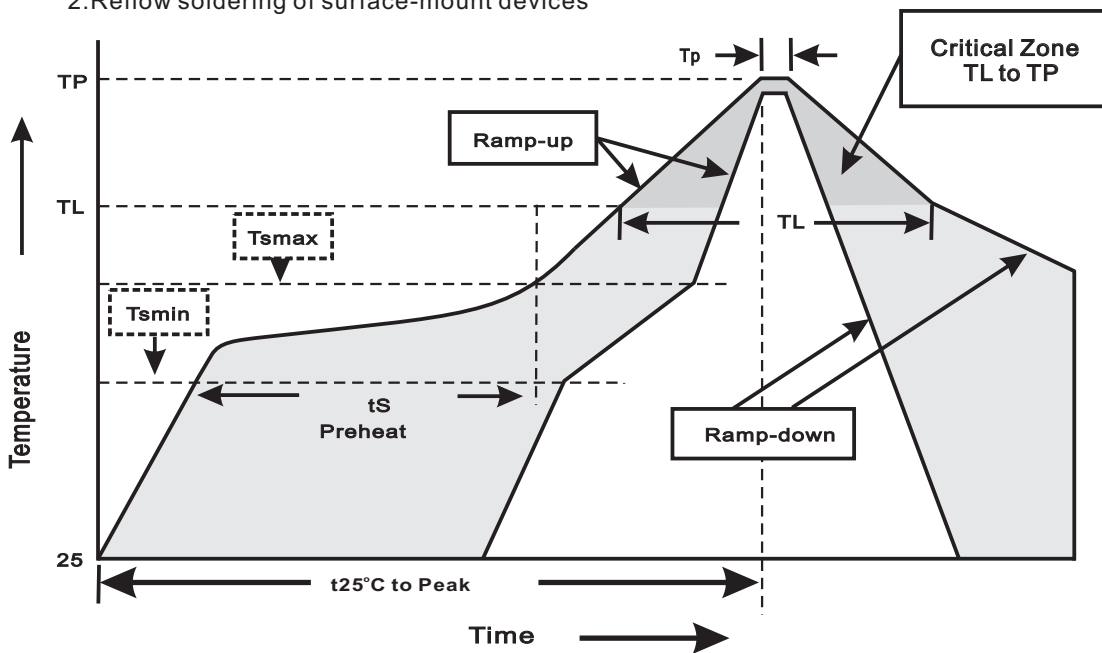
BAS16W/BAV70W/BAW56W/BAV99W/BAL99W

Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA, (m/m)	CARTON SIZE (m/m)	CARTON (pcs)	APPROX. GROSS WEIGHT (kg)
SOT-323	7"	3,000	4.0	30,000	183*183*123	178	382*262*387	240,000	9.5

Suggested thermal profiles for soldering processes

- 1.Storage environment: Temperature=5°C~40°C Humidity=55%±25%
- 2.Reflow soldering of surface-mount devices



3.Reflow soldering

Profile Feature	Soldering Condition
Average ramp-up rate(TL to TP)	<3°C/sec
Preheat -Temperature Min(Tsmin) -Temperature Max(Tsmax) -Time(min to max)(ts)	150°C 200°C 60~120sec
Tsmax to TL -Ramp-upRate	<3°C/sec
Time maintained above: -Temperature(TL) -Time(tL)	217°C 60~260sec
Peak Temperature(TP)	255°C-0/+5°C
Time within 5°C of actual Peak Temperature(tp)	10~30sec
Ramp-down Rate	<6°C/sec
Time 25°C to Peak Temperature	<6minutes

BAS16W/BAV70W/BAW56W/BAV99W/BAL99W**High reliability test capabilities**

Item Test	Conditions	Reference
1. Solder Resistance	at 260±5°C for 10±2sec. immerse body into solder 1/16"±1/32"	MIL-STD-750D METHOD-2031
2. Solderability	at 245±5°C for 5 sec.	MIL-STD-202F METHOD-208
3. High Temperature Reverse Bias	$V_R=80\%$ rate at $T_J=150^\circ\text{C}$ for 168 hrs.	MIL-STD-750D METHOD-1038
4. Forward Operation Life	Rated average rectifier current at $T_A=25^\circ\text{C}$ for 500hrs.	MIL-STD-750D METHOD-1027
5. Intermittent Operation Life	$T_A = 25^\circ\text{C}$, $I_F = I_o$ On state: power on for 5 min. off state: power off for 5 min. on and off for 500 cycles.	MIL-STD-750D METHOD-1036
6. Pressure Cooker	15P _{SIG} at $T_A=121^\circ\text{C}$ for 4 hrs.	JESD22-A102
7. Temperature Cycling	-55°C to +125°C dwelled for 30 min. and transferred for 5min. total 10 cycles.	MIL-STD-750D METHOD-1051
8. Forward Surge	Peak Forward Surge Current	MIL-STD-750D METHOD-4066-2
9. Humidity	at $T_A=85^\circ\text{C}$, RH=85% for 1000hrs.	MIL-STD-750D METHOD-1021
10. High Temperature Storage Life	at 175°C for 1000 hrs.	MIL-STD-750D METHOD-1031